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Docket No.: 2328-062

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

DHINDSA, Rajinder

U.S. Patent Application No. 10/645,665

Group Art Unit: 2821

Filed: August 22, 2003

Examiner: TUNG X LE

For: MULTIPLE FREQUENCY PLASMA ETCH REACTOR

DECLARATION UNDER 37 CFR 1.131 TRANSMITTAL LETTER


Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The forwarded Declaration includes the signatures of the remaining inventors.
Consideration of the Declaration is in order.

Respectfully submitted,

LOWE HAUPTMAN HAM & BERNER, LLP



Allan M. Lowe
Registration No. 19,641

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Date: December 7, 2007

CERTIFICATION OF FACSIMILE TRANSMISSION
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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

DHINDSA, Rajinder *et al.*

Confirmation No. 8414

U.S. Patent Application No. 10/645,665

Group Art Unit: 2821

Filed: August 22, 2003

Examiner: Tung X Le

For: MULTIPLE FREQUENCY PLASMA ETCH REACTOR

DECLARATION UNDER 37 CFR 1.131

We, Rajinder Dhindsa, Eric Lenz, Mukund Srinivasan, Aaron Eppler, Lumin Li, Felix Kozakevich, Camelia Rusu, Dave Trussel, Reza Sadjadi, Jim Tietz, and Jeff Marks, the applicants of the referenced application hereby declare as follows:

1. Prior to August 1, 2003, we successfully reduced to practice a vacuum plasma processor comprising a vacuum chamber having a (a) lower electrode including an electrostatic chuck (ESC) that carried a workpiece in the form of a semiconductor wafer and (b) an upper electrode, wherein a frequency of 40 MHz was applied to the upper electrode and frequencies of 27 MHz and 2 MHz were applied to the bottom electrode. Exhibit 1 is a cross-sectional view of the vacuum chamber that was operated under these conditions. The vacuum chamber illustrated in Exhibit 1 was modified so that (a) 47 MHz (instead of 27 MHz) was applied to the upper electrode at the same time that (b) 27 MHz and 2 MHz (instead of 2 MHz) were applied to the 200 mm electrostatic chuck (ESC) included in the bottom electrode.

2. Exhibits 2 and 3 are microphotographs of three different semiconductor wafers that were successfully etched prior to August 1, 2003 with the arrangement described in Paragraph 1, wherein the upper and lower electrodes are respectively indicated in Exhibits 2 and 3 by UE and LE. The microphotographs of Exhibits 2 and 3 include dates that are prior to August 1, 2003, but have been redacted.

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3. For the left microphotographs of Exhibits 2 and 3, 900 W at 40 MHz was applied to the upper electrode, while 300 W at 27 MHz and 1800 W at 2 MHz were applied to the lower electrode. For the center microphotographs of Exhibits 2 and 3, 600 W at 40 MHz was applied to the upper electrode, while 600 W at 27 MHz and 1800 W at 2 MHz were applied to the bottom electrode. For the right and microphotographs of Exhibits 2 and 3, 300 W at 40 MHz was applied to the upper electrode, while 900 W at 27 MHz and 1800 watts at 2 MHz were applied to the bottom the electrode. In all instances, the vacuum chamber was operated at a vacuum pressure of 50 millitorr and the etchant, i.e., processing, gas was a mixture of argon, C4F8 and oxygen.

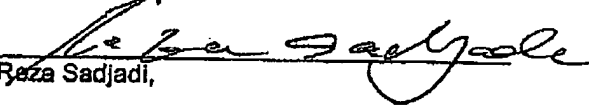
4. The microphotographs of Exhibits 2 and 3 include clear indications of holes that were successfully bored into the semiconductor wafers and that the holes bored in the different wafers had different characteristics for the different powers that were applied to the different frequencies.

We hereby declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine, or imprisonment, or both, under

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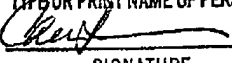
Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

DATED this _____ day of September, 2007, at _____.


Rajinder Dhindsa,
Eric Lenz
Mukund Srinivasan,
Aaron Eppler
Lumin Li,
Felix Kozakevich
Camella Rusu
Dave Trussel
Reza Sadjadi,
Jim Tietz
Jeff Marks

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DATED this _____ day of September, 2007, at _____



Rajinder Dhindsa,


Eric Lenz


Mukund Srinivasan,

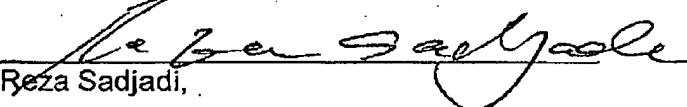

Aaron Eppler


Lumin Li,


Felix Kozakevich

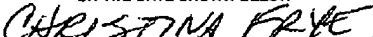

Camelia Rusu


Dave Trussel


Reza Sadjadi,

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DATE

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